

ABSTRACT OF THE DISCLOSURE

A cost-efficient and reliable method for assessing lateral dopant profiles includes the estimation of a reference profile formed below a gate structure of a transistor device. The overlap capacitance is then determined for at least two different overlaps, created by different
5 spacer widths, and the lateral extension of a dopant profile to be measured, is estimated on the basis of a relationship between overlap capacitance and spacer width for the reference dopant profile.